

Amendments to the Specification

Please replace paragraph 0048 with the following rewritten paragraph:

-- The fine porous region 16b [[16a]] is located mostly at the bottom of porous region 16, while the courser porous region 16a [[16b]] is located mostly at the top of porous region 16. The fine porous region is less dense (i.e., contains a lower number of pores) as compared to the courser porous Si region. As the surface area of the fine porous Si is immensely large, any type of surface reaction, including oxidation, would occur faster in the fine porous Si region than the courser porous Si region because of a higher surface area. --